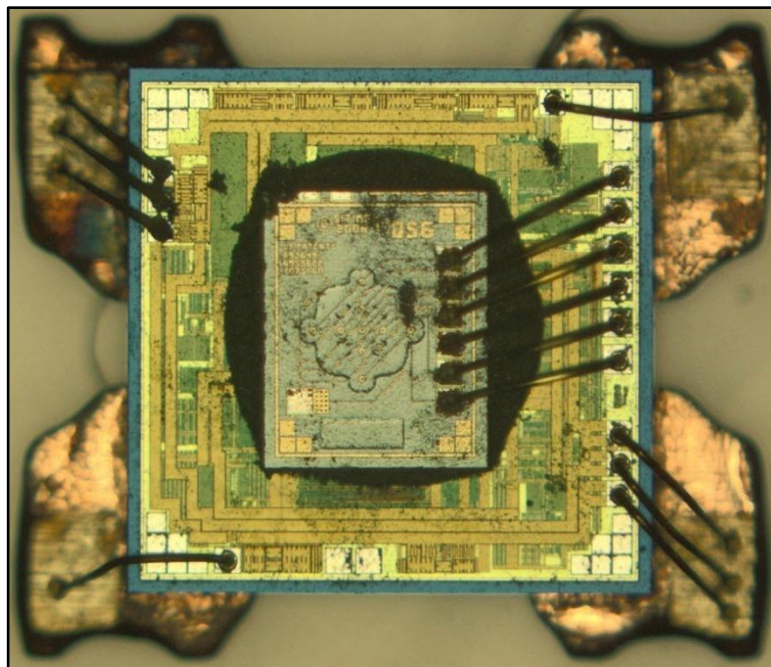


# Reverse Costing analysis



## SiTime SiT8002 MEMS Oscillator

December 2009 - Version 1

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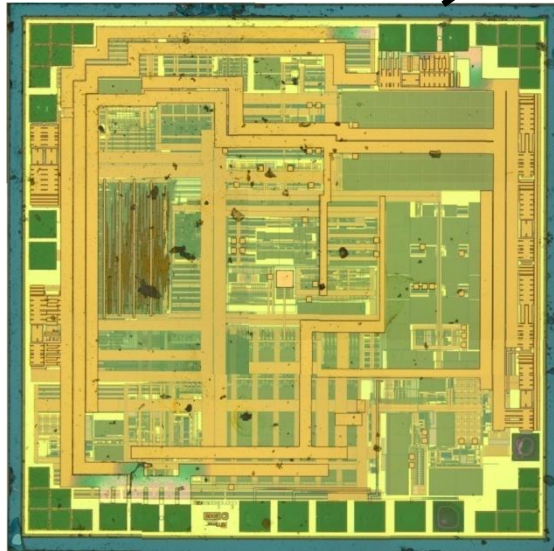
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SiT8002



ASIC



CMOS process

x.xxµm, x metallization layers, x polysilicon Layers  
xx Lithography steps

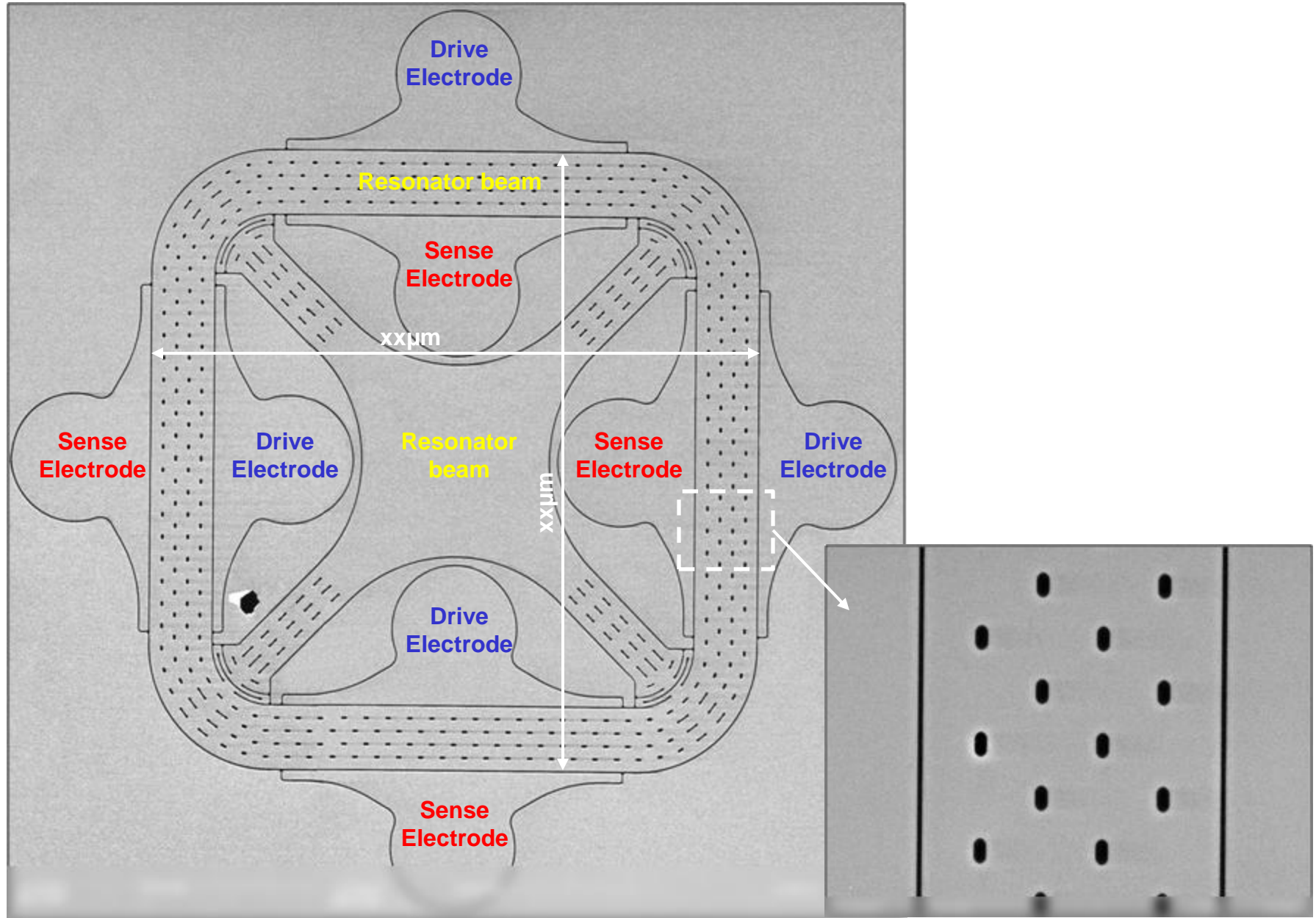
Assembly in package  
Encapsulation  
Final test

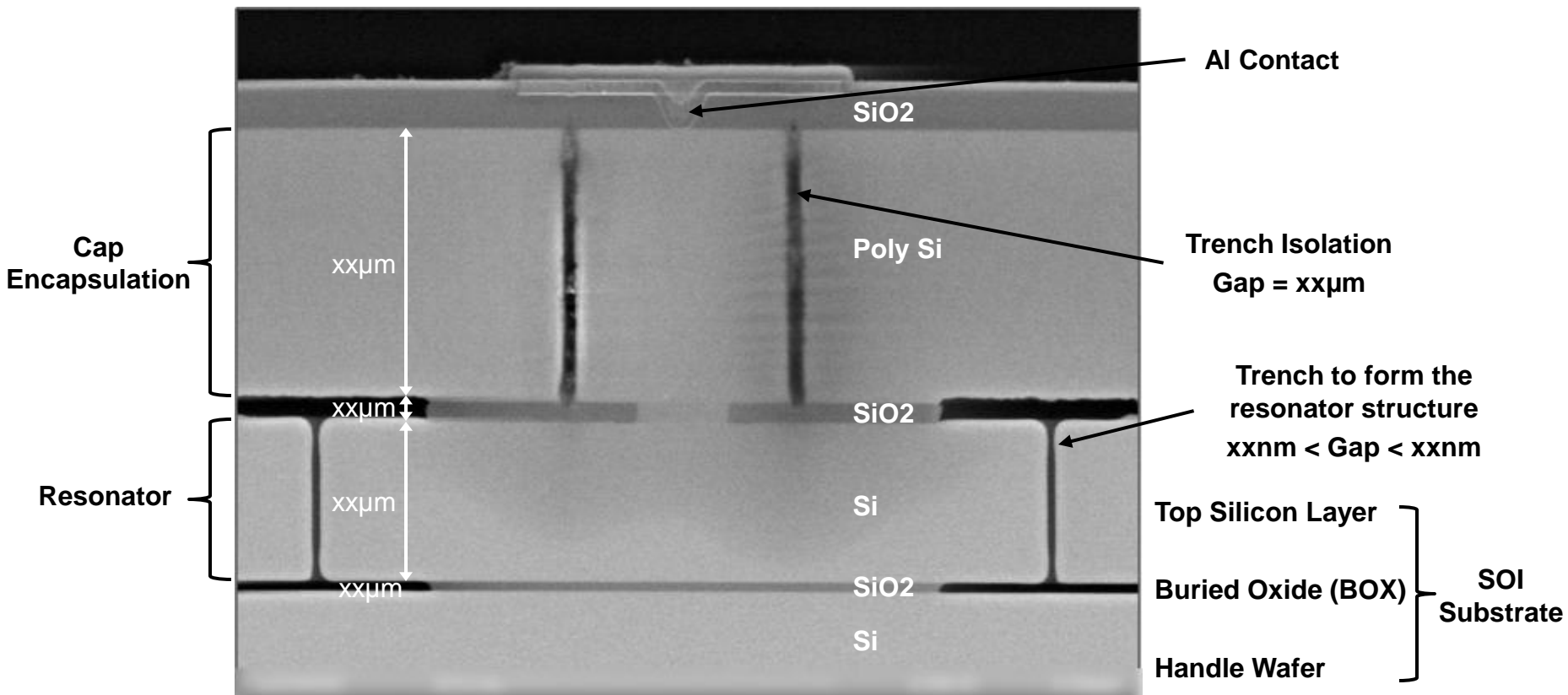
MEMS Resonator



SOI Substrate

Sealed with EpiSeal™ Process  
xx Lithography steps





MEMS Cross section

A **Bonded SOI wafer** is used to realize the **xxµm top Silicon layer**. The resonator structure is formed in the top silicon layer by **DRIE**. An **oxide sacrificial layer (xxµm)** is deposited by LPCVD on the silicon resonator.

The **xxµm of polysilicon** is deposited in an epitaxial reactor and is used to seal the resonator. Trench isolation are made in the polysilicon layer by **DRIE**.

• The MEMS is manufactured by xxxx in the 200mm xxxx foundry:

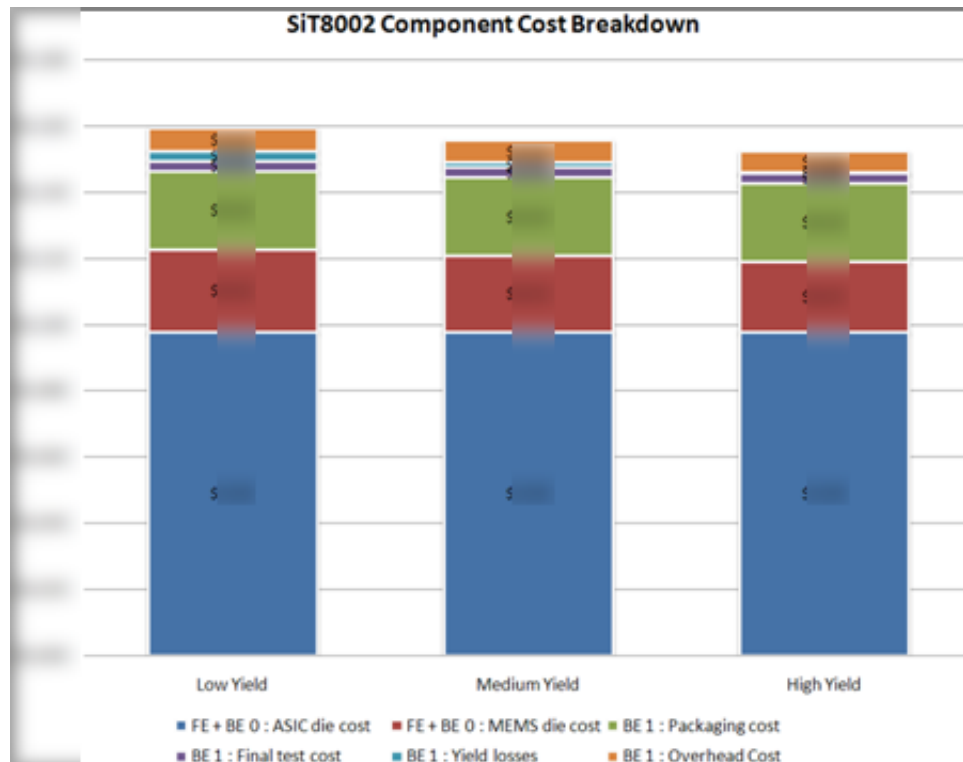
- Process type: MEMS/IC/PT/ Hybrid/PT
- Metal layers: 1/2/3
- Polysilicon layer: 1/2
- Lithography steps: 1/2

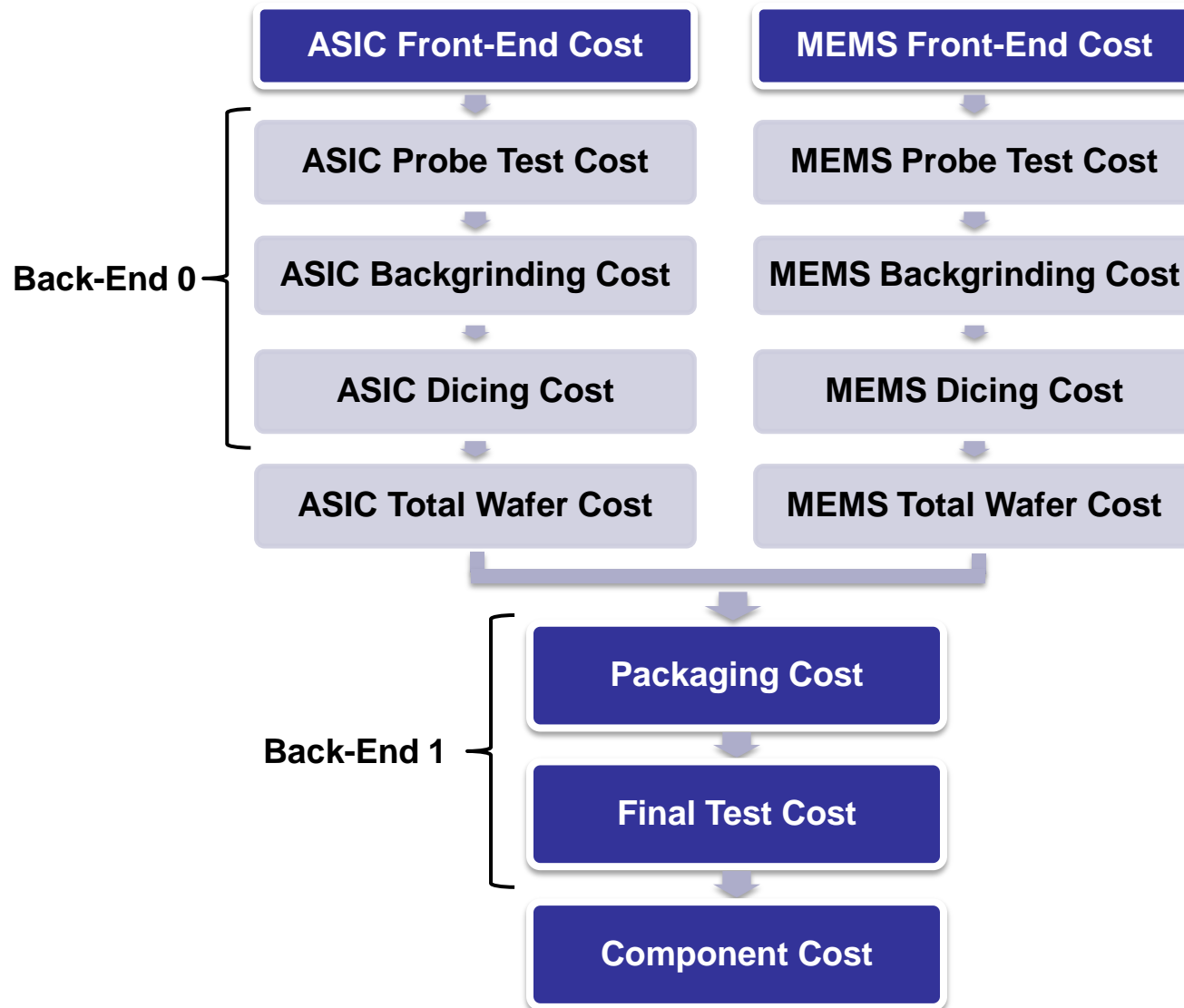
The cavity formed by the release process is cleaned in a dry and controlled chemical reaction. During the cleaning process the walls are etched forming a recessed cavity. A thermal polysilicon layer (up to 100nm) is then deposited in the recessed cavity to seal the structure. This encapsulation layer is then patterned and etched by DRIE to form isolated contacts. An oxide layer (up to 100nm) is then deposited, patterned and etched to make self electrical contact area. An Aluminum layer (up to 100nm) is then deposited, patterned and etched to make the electrical interconnections and bond pads. Two layers of oxide (up to 100nm) and a silicon nitride (up to 100nm) are then deposited to protect the electrical interconnections. These protective layers are then patterned and etched to open the Aluminum bond pads.

Encapsulation & Electrical Contacts



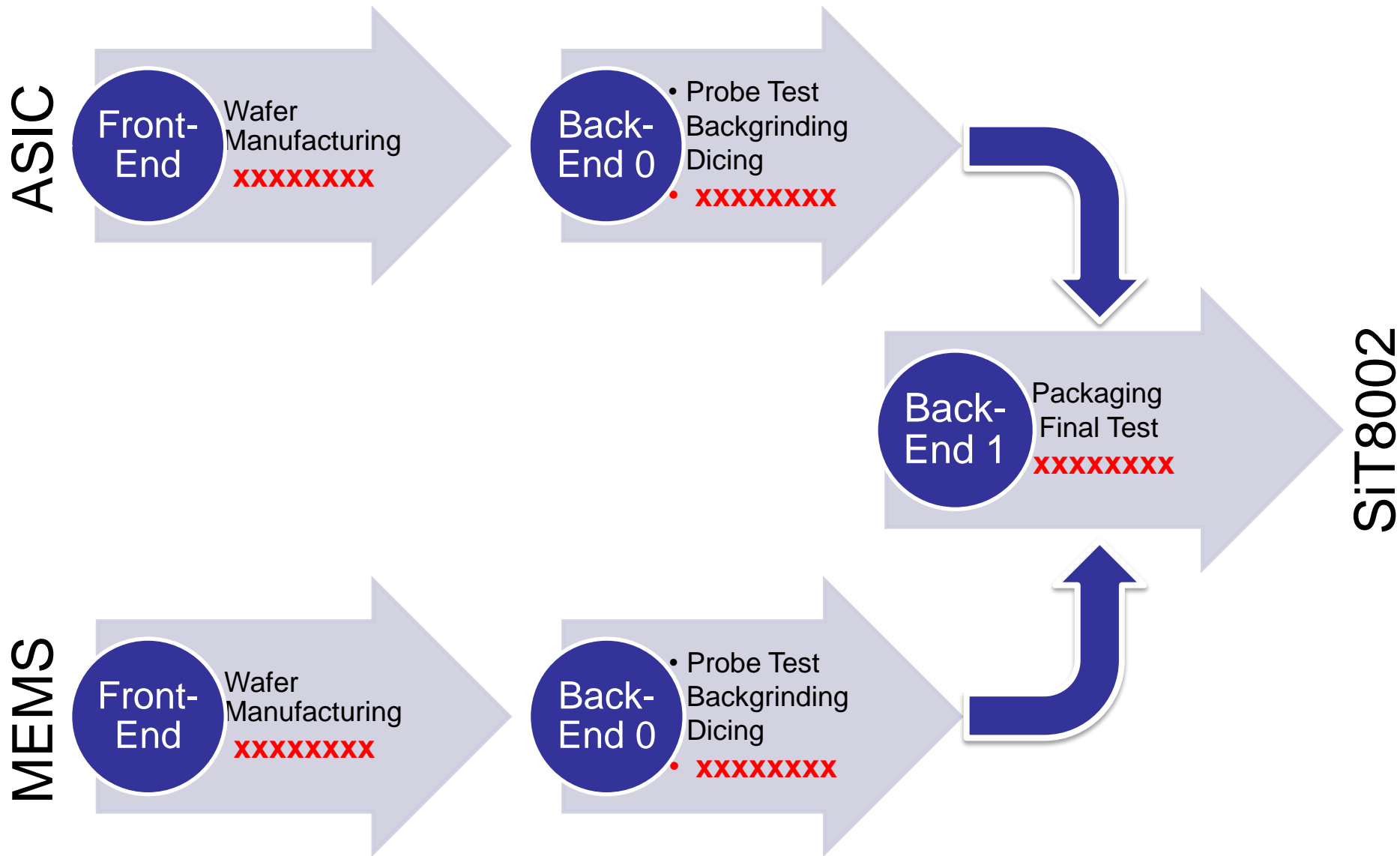
- The SiT8002 component is designed by SiTime Corporation.
- The production of the ASIC by xxx is assumed to take place in the 200mm xxx wafer foundry in xxx.
  - The ASIC wafer cost is estimated at \$xxx, the die cost is estimated at \$xxx
- The production of the MEMS by xxx is assumed to take place in the 200mm xxx fab in xxx.
  - The MEMS wafer cost is estimated at \$xxx, the die cost is estimated at \$xxx.
- The packaging of the two dies by xxx is assumed to take place in xxx.
  - The packaging cost is estimated at \$xxx.
- The component manufacturing cost range from \$xxx to \$xxx according to yield hypotheses.





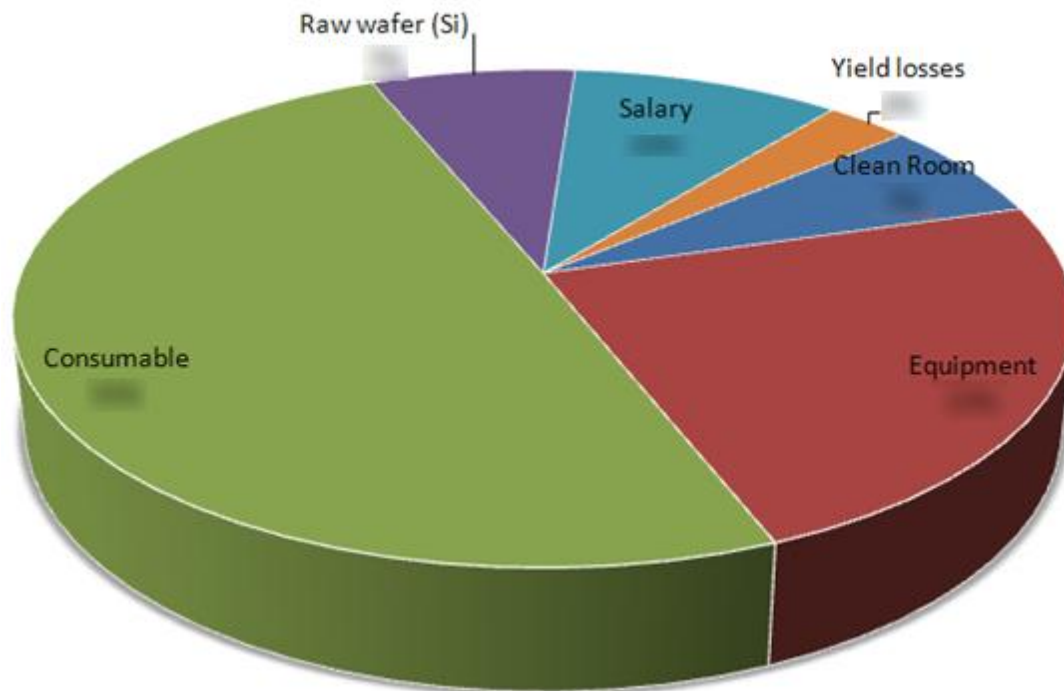
- We perform the economic analysis of the ASIC with the [IC Purchaser](#) software.
- We perform the economic analysis of the MEMS and the packaging with the [MEMS CoSim+](#) software.





	Low Yield		Medium Yield		High Yield	
	Cost	Breakdown	Cost	Breakdown	Cost	Breakdown
Clean Room						
Equipment						
Consumable						
Raw wafer (Si)						
Salary						
Yield losses						
<b>Front-End Cost</b>						
<b>Cost with Foundry Overhead</b>						

**ASIC Unprobed Wafer Cost Breakdown (Middle Yield)**

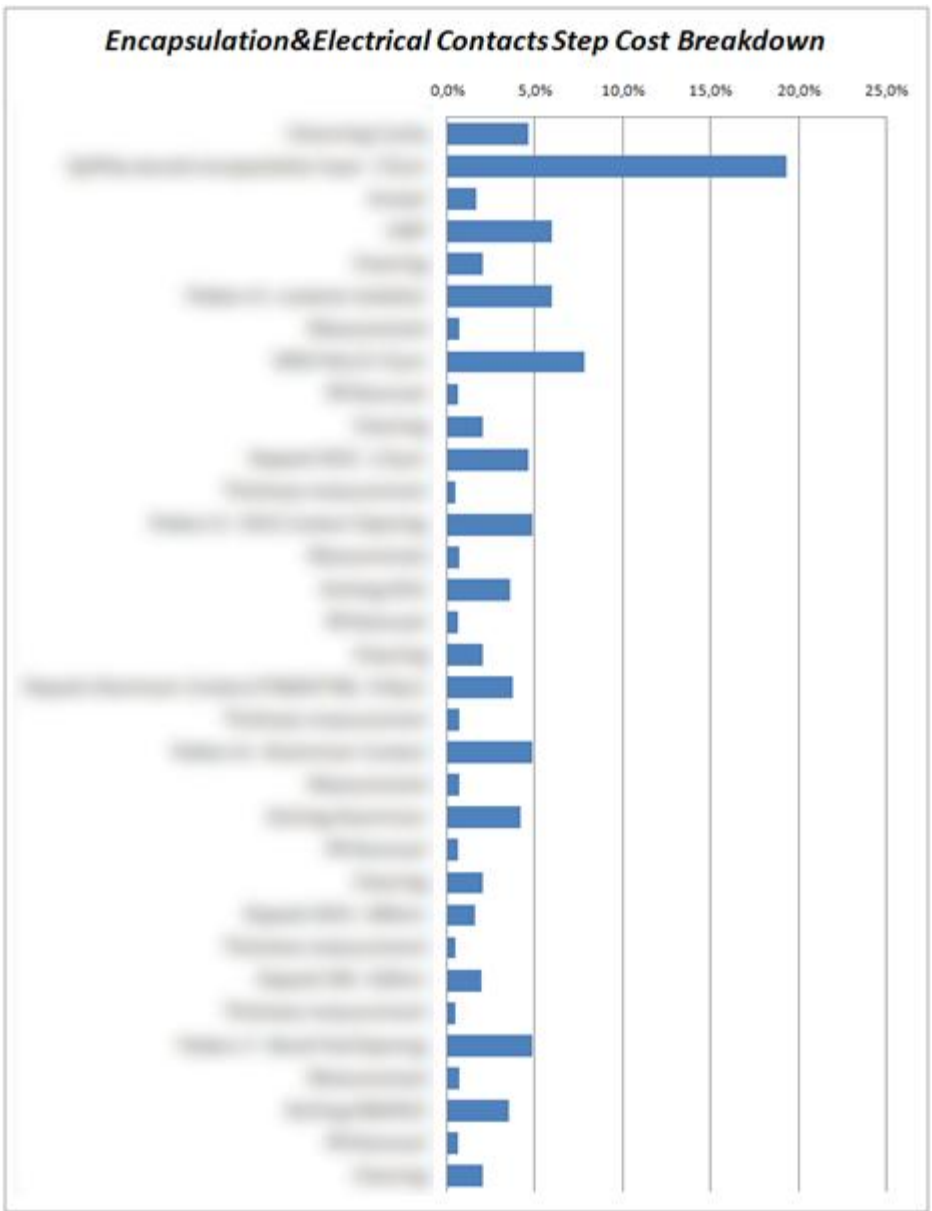


- Very low wafer cost decrease because the technology is mature.

- The main part of the wafer cost is due to the consumables with xx%. The salary part is xx%. This is an average value for production in xxx.

- The manufacturing yield ranges from xx% to xx%. The mature technology explains these values.

Encapsulation & Electrical Contacts	Cost	Breakdown
	\$	4,6%
	\$	19,3%
	\$	1,7%
	\$	6,0%
	\$	2,0%
	\$	6,0%
	\$	0,7%
	\$	7,8%
	\$	0,6%
	\$	2,0%
	\$	4,6%
	\$	0,5%
	\$	4,9%
	\$	0,7%
	\$	3,6%
	\$	0,6%
	\$	2,0%
	\$	3,7%
	\$	0,7%
	\$	4,9%
	\$	0,7%
	\$	4,2%
	\$	0,6%
	\$	2,0%
	\$	1,6%
	\$	0,5%
	\$	1,9%
	\$	0,5%
	\$	4,9%
	\$	0,7%
	\$	3,5%
	\$	0,6%
	\$	2,0%
<b>TOTAL</b>	<b>\$</b>	



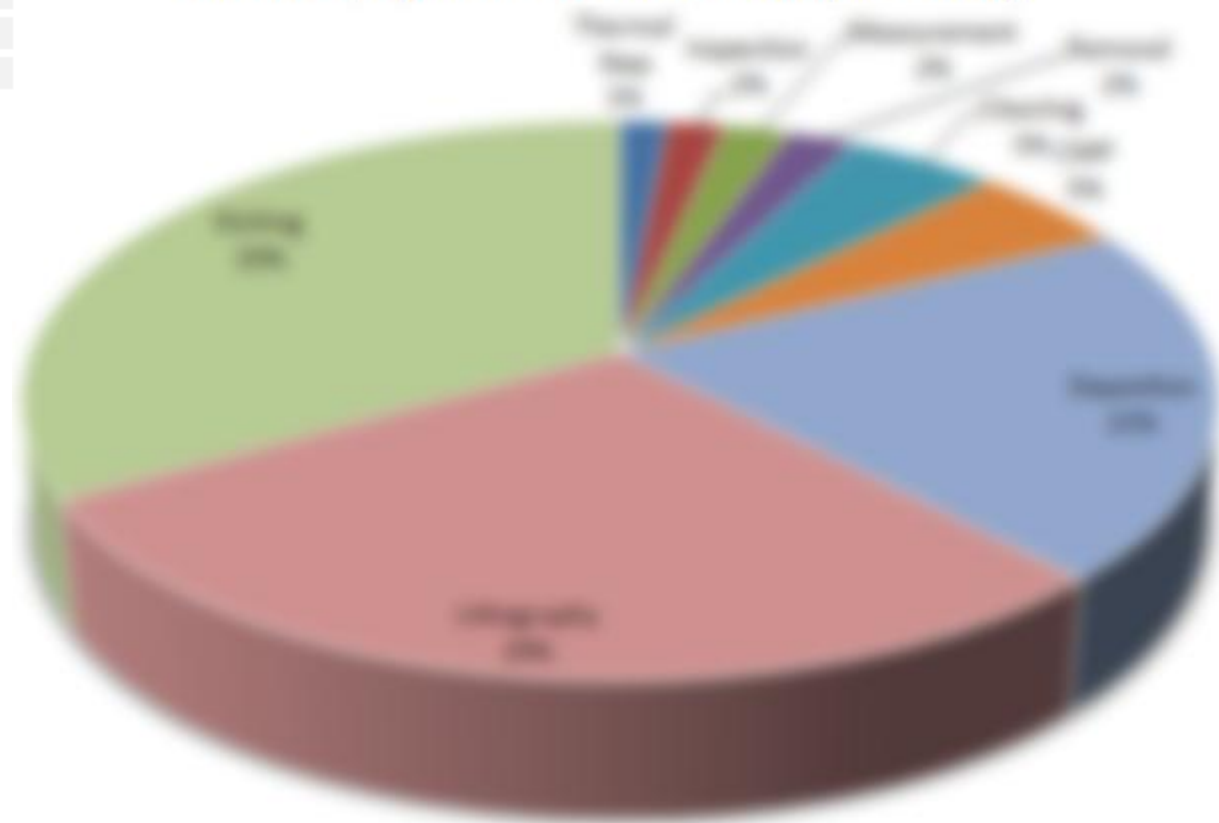
### Encapsulation Steps Cost

Equipment Family	Equipment Cost	Breakdown
Thermal Step	\$	%
Inspection	\$	%
Measurement	\$	%
Removal	\$	%
Cleaning	\$	%
CMP	\$	%
Deposition	\$	%
Lithography	\$	%
Etching	\$	%
<b>TOTAL</b>	<b>\$</b>	

- The main part of the equipment cost is due to the xxx steps (xx%). The xxxx explain this result.

- Details of the equipment cost per step are given in the Excel Spreadsheet.

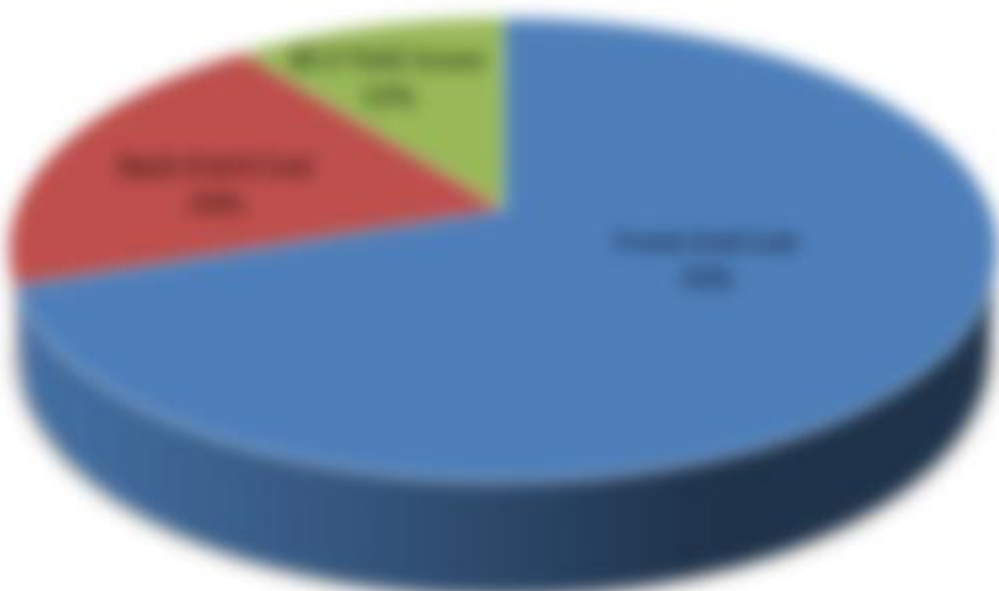
*MEMS Equipment Cost Breakdown per Family*



*MEMS Equipment Cost per Family  
(Simulated with MEMS CoSim+ Cost Simulation Tool)*

	Low Yield		Medium Yield		High Yield	
	Cost	Breakdown	Cost	Breakdown	Cost	Breakdown
Front-End Cost with Overhead						
Back-End 0 Cost with Overhead						
<b>MEMS Wafer Cost</b>						
Nb of potential dies per wafer						
Nb of good dies per wafer						
Front-End Cost						
Back-End 0 Cost						
BE 0 Yield losses						
<b>MEMS Die Cost</b>						

**MEMS Die Cost Breakdown (Medium Yields)**



- The final MEMS die cost range from \$xx to \$xx according to yield variations.
- The back-end 0 cost (probe test, backgrinding and dicing) represent xx% of the cost of the die.
- The yield losses costs due to probe and dicing represent xx% of the total manufacturing cost.
  - The MEMS cost includes the rejects at probe test and dicing.
  - The yield losses represents the bad dies out for the garbage.

- **Standard MLF (QFN type) package.**
  - ✓ **4-Lands**
  - ✓ **2.50 x 2.00 x 0.75mm**
- **2 dies to be assembled in the package**
  - ✓ **ASIC : xxxmm<sup>2</sup>**
  - ✓ **MEMS : xxxmm<sup>2</sup>**
  - ✓ **Stacked dies (conductive epoxy between the two dies)**
  - ✓ **8 bondings ASIC → Leadframe**
    - **Gold, xxμm diameter, ~1mm length**
  - ✓ **6 bondings MEMS → ASIC**
    - **Gold, xxμm diameter, ~1mm length**
- **The assembly is done by xxx in xxx.**
- **The packaging cost is estimated to \$xx per component.**
- **The packaging yield is estimated to range from xx% to xx%.**

